

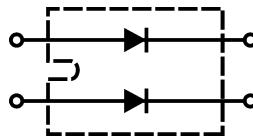
Fast Recovery Epitaxial Diode (FRED)

DSEI 2x 101

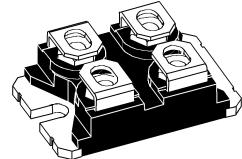
V_{RRM} = 600 V
I_{FAVM} = 2x 96 A
t_{rr} = 35 ns

Preliminary data

V _{RSM}	V _{RRM}	Type
V	V	
600	600	DSEI 2x 101-06A



miniBLOC, SOT-227 B
 **E72873**



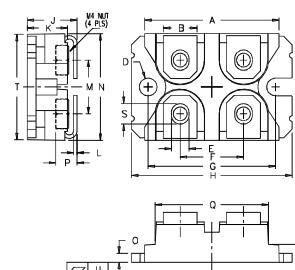
Symbol	Test Conditions	Maximum Ratings (per diode)	
I _{F(RMS)}	T _{VJ} = T _{VJM}	150	A
I _{F(AVM} ①	T _C = 70°C; rectangular, d = 0.5	96	A
I _{FRM}	t _p < 10 µs; rep. rating, pulse width limited by T _{VJM}	TBD	A
I _{FSM}	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine	1200	A
	t = 8.3 ms (60 Hz), sine	1300	A
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	1080	A
	t = 8.3 ms (60 Hz), sine	1170	A
I ² t	T _{VJ} = 45°C t = 10 ms (50 Hz), sine	7200	A ² s
	t = 8.3 ms (60 Hz), sine	7100	A ² s
	T _{VJ} = 150°C; t = 10 ms (50 Hz), sine	5800	A ² s
	t = 8.3 ms (60 Hz), sine	5700	A ² s
T _{VJ}		-40...+150	°C
T _{VJM}		150	°C
T _{stg}		-40...+150	°C
P _{tot}	T _C = 25°C	250	W
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	2500	V~
M _d	Mounting torque Terminal connection torque (M4)	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		30	g

Symbol	Test Conditions	Characteristic Values (per diode)	
		typ.	max.
I _R	T _{VJ} = 25°C V _R = V _{RRM}	3	mA
	T _{VJ} = 25°C V _R = 0.8 • V _{RRM}	1	mA
	T _{VJ} = 125°C V _R = 0.8 • V _{RRM}	20	mA
V _F	I _F = 100 A; T _{VJ} = 150°C	1.17	V
	T _{VJ} = 25°C	1.25	V
V _{To} r _T	For power-loss calculations only	0.70 4.7	V mΩ
R _{thJC} R _{thCH}		0.05	K/W K/W
t _{rr}	I _F = 1 A; -di/dt = 400 A/µs; V _R = 30 V; T _{VJ} = 25°C	35	50 ns
I _{RM}	V _R = 100 V; I _F = 80 A; -di _F /dt = 200 A/µs L ≤ 0.05 mH; T _{VJ} = 100°C	19	24 A

① I_{FAVM} rating includes reverse blocking losses at T_{VJM}; V_R = 0.8 V_{RRM}, duty cycle d = 0.5
Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.5	31.7	1.241	1.249
B	7.8	8.2	0.307	0.323
C	4.0	-	0.158	-
D	4.1	4.3	0.162	0.169
E	4.1	4.3	0.162	0.169
F	14.9	15.1	0.587	0.595
G	30.1	30.3	1.186	1.193
H	38.0	38.2	1.497	1.505
J	11.8	12.2	0.465	0.481
K	8.9	9.7	0.351	0.382
L	0.75	0.85	0.030	0.033
M	12.6	12.8	0.496	0.504
N	25.2	25.4	0.993	1.001
O	1.95	2.05	0.077	0.081
P	-	5.0	-	0.197

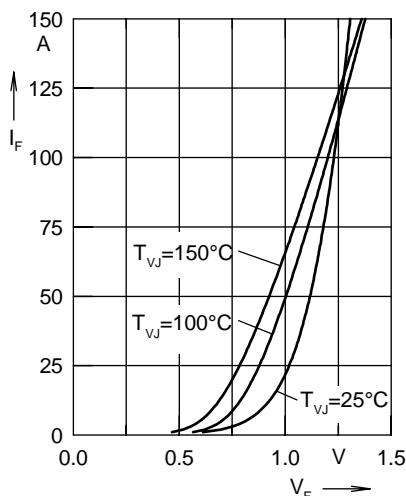


Fig. 1 Forward current I_F versus V_F

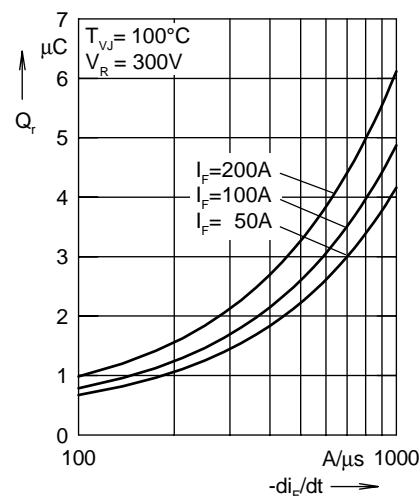


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

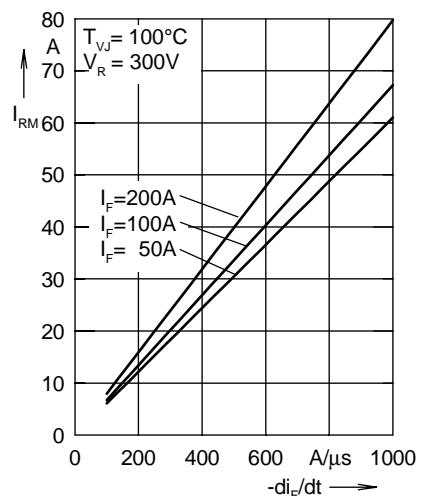


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

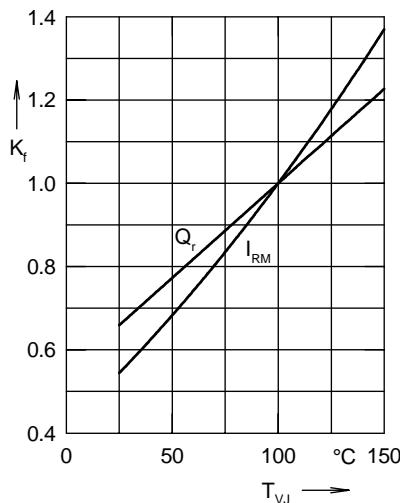


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

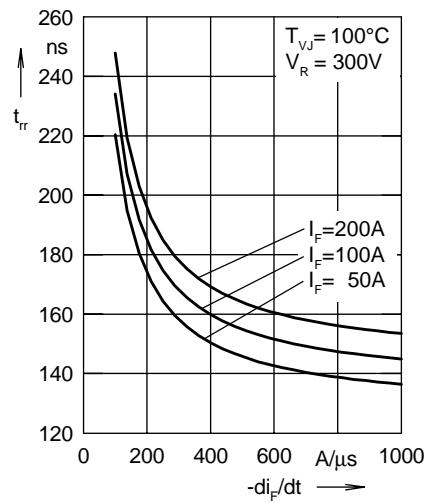


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

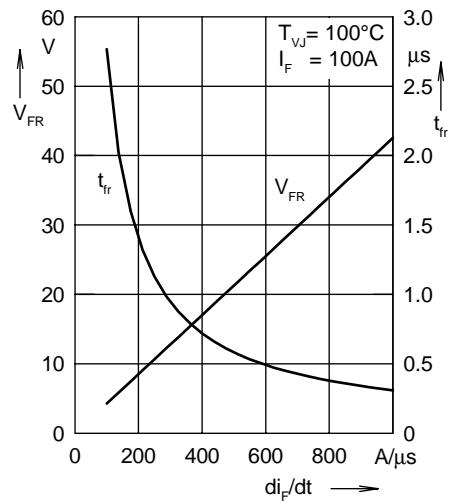


Fig. 6 Peak forward voltage V_{FR} and t_{rr} versus di_F/dt

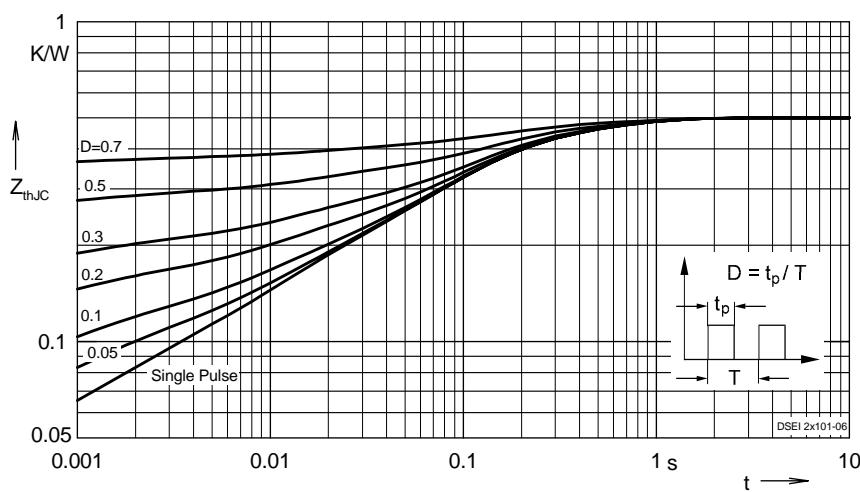


Fig. 7 Transient thermal impedance junction to case at various duty cycles

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.02	0.00002
2	0.05	0.00081
3	0.076	0.01
4	0.24	0.94
5	0.114	0.45